The RF Line Microwave Pulse Power Transistor

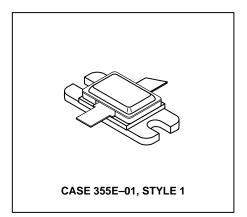
Designed for 1025–1150 MHz pulse common base amplifier applications such as DME.

- Guaranteed Performance @ 1090 MHz
 Output Power = 500 Watts Peak
 Gain = 5.2 dB Min
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- · Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- · Internal Input Matching
- Characterized with 10 μs, 1.0% Duty Cycle Pulses

MRF1500

Motorola Preferred Device

500 W (PEAK), 1025-1150 MHz MICROWAVE POWER TRANSISTOR NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	65	Vdc
Collector–Base Voltage	V _{СВО}	65	Vdc
Emitter–Base Voltage	VEBO	3.5	Vdc
Collector Current — Peak (1)	IC	35	Adc
Total Device Dissipation @ T _C = 25°C (1), (2) Derate above 25°C	PD	1750 10	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +200	°C
Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.1	°C/W

NOTES:

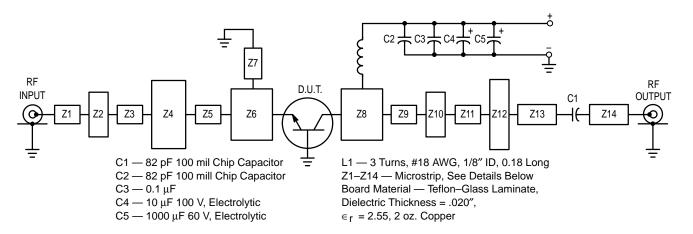
- 1. Under pulse RF operating conditions.
- 2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
- 3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @32 μs, 2.0%)

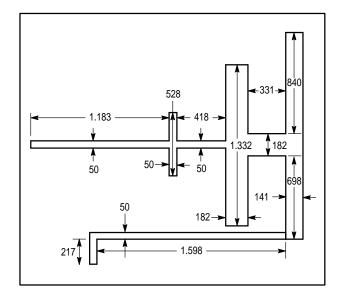
Preferred devices are Motorola recommended choices for future use and best overall value.



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 60 mAdc, V _{BE} = 0)	V(BR)CES	70	_	_	Vdc
Collector-Base Breakdown Voltage (I _C = 60 mAdc, I _E = 0)	V(BR)CBO	70	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0)	ICBO	_	_	40	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 5.0 Vdc)	hFE	20	40	_	_
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	G _{PB}	5.2	_	_	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	η	37	_	_	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz, Load VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power			





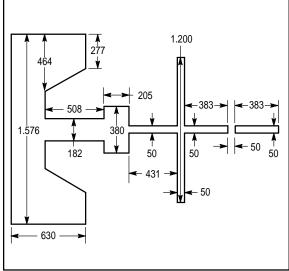


Figure 1. Test Circuit

TYPICAL CHARACTERISTICS

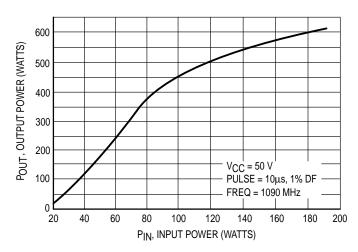
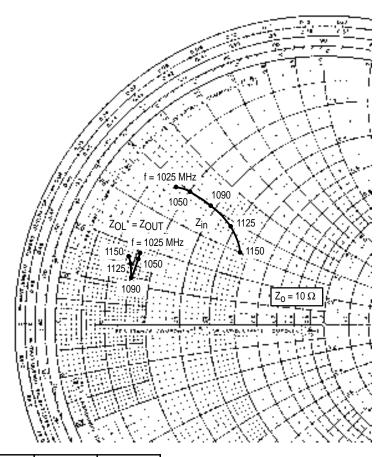


Figure 2. Output Power versus Input Power

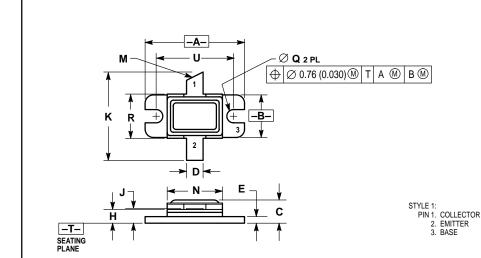


f MHz	Z _{in} OHMS	z _{oL} *
1025	1.6 + j3.9	1.6 + j1.7
1050	2.0 + j4.0	1.6 + j1.6
1090	2.8 + j4.0	1.5 + j1.1
1125	3.9 + j3.8	1.5 + j1.4
1150	4.6 + j3.0	1.4 + j1.6

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device operates at a given output power, voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.890	0.910	22.61	23.11
В	0.375	0.395	9.53	10.03
С	0.190	0.210	4.83	5.33
D	0.145	0.155	3.69	3.93
Е	0.055	0.065	1.40	1.65
Н	0.120	0.130	3.05	3.30
J	0.003	0.006	0.08	0.15
K	0.770	0.830	19.56	21.08
М	45°REF		45°REF	
N	0.490	0.510	12.45	12.95
Q	0.115	0.125	2.93	3.17
R	0.395	0.405	10.04	10.28
U	0.700 BSC		17.78	BSC

CASE 355E-01 ISSUE A

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and

Literature Distribution Centers:

USA: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036.

EUROPE: Motorola Ltd.; European Literature Centre; 88 Tanners Drive, Blakelands, Milton Keynes, MK14 5BP, England.

JAPAN: Nippon Motorola Ltd.; 4-32-1, Nishi-Gotanda, Shinagawa-ku, Tokyo 141, Japan.

ASIA PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Center, No. 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong.



